**In the Claims**

Claims 1-18 (canceled).

Claim 19 (currently amended): A method of forming a semiconductor construction, comprising:

providing a semiconductor substrate;

forming a first layer comprising silicon and nitrogen over the substrate;

forming a second layer comprising at least 50 weight% carbon over and physically against the first layer; ~~and~~

forming a third layer consisting essentially of a photoresist system over and physically against the second layer;

exposing the photoresist system to patterned light and subsequently heating the photoresist system; the second layer releasing acid into the photoresist system during the heating; and

after the heating, exposing the photoresist system to a developing solvent.

Claim 20 (cancelled).

Claim 21 (original): The method of claim 19 wherein the first layer comprises silicon, oxygen and nitrogen.

Claim 22 (original): The method of claim 19 wherein the first layer consists essentially of silicon oxynitride.

Claim 23 (original): The method of claim 19 wherein the forming the second layer comprises spin-coating the second layer across the first layer.

Claim 24 (original): The method of claim 19 wherein the second layer comprises a surfactant.

Claim 25 (original): The method of claim 19 wherein the second layer comprises a polymer.

Claim 26 (original): The method of claim 19 wherein the second layer comprises a cross-linked polymer.

Claim 27 (original): The method of claim 19 wherein the second layer comprises an acrylic polymer.

Claim 28 (original): The method of claim 19 wherein the second layer comprises a component that absorbs light having a wavelength within a region from 150 nanometers to 250 nanometers.

Claim 29 (original): A method of forming a semiconductor construction, comprising:

providing a semiconductor substrate;

forming a first layer comprising silicon and nitrogen over the substrate;

forming a second layer comprising at least 50 weight% carbon over the first layer;

forming a third layer consisting essentially of a photoresist system over and physically against the second layer;

exposing a first portion of the third layer radiation while not exposing a second portion to the radiation;

subjecting the third layer to conditions which cause either the exposed first portion or unexposed second portion of the photoresist system to release acid; the second layer also releasing acid as the third layer is exposed to the conditions; and

after subjecting the third layer to the conditions, removing either the first or second portion selectively relative to the other of the first and second portion.

Claim 30 (original): The method of claim 29 wherein the conditions which cause either the exposed first portion or unexposed second portion of the photoresist system to release acid comprise heating of the third layer to a temperature of at least about 90°C.

Claim 31 (original): The method of claim 29 wherein the first layer comprises silicon, oxygen and nitrogen.

Claim 32 (original): The method of claim 29 wherein the first layer consists essentially of silicon oxynitride.

Claim 33 (original): The method of claim 29 wherein the forming the second layer comprises spin-coating the second layer across the first layer.

Claim 34 (original): The method of claim 29 wherein the second layer comprises a surfactant.

Claim 35 (original): The method of claim 29 wherein the second layer comprises a polymer.

Claim 36 (original): The method of claim 29 wherein the second layer comprises a cross-linked polymer.

Claim 37 (original): The method of claim 29 wherein the second layer comprises an acrylic polymer.

Claim 38 (original): The method of claim 29 wherein the second layer comprises a component that absorbs light having a wavelength within a region from 150 nanometers to 250 nanometers.